Notice of Allowability	Application No.	Applicant(s)	
	10/017,832 Examiner	YANG ET AL.	
	Examiner	Art Unit	
	Russell M Kobert	2829	
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT Report of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED or other appropriate comm IGHTS. This application is	in this application. If not include nunication will be mailed in due of	d course. THIS
 This communication is responsive to the Election filed on an an accepted by the allowed claim(s) is/are 1-9. The drawings filed on 12 December 2001 are accepted by Acknowledgment is made of a claim for foreign priority und a) All b) Some* c) None of the: Certified copies of the priority documents have Certified copies of the priority documents have 	the Examiner. der 35 U.S.C. § 119(a)-(d) be been received. been received in Applicat	ion No	
 Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). 	cuments have been receiv	ed in this national stage applicat	on from the
* Certified copies not received: 5. Acknowledgment is made of a claim for domestic priority upon (a) The translation of the foreign language provisional a 6. Acknowledgment is made of a claim for domestic priority upon the foreign language.	pplication has been receiv	ed.	
Applicant has THREE MONTHS FROM THE "MAILING DATE" of below. Failure to timely comply will result in ABANDONMENT of			
7. A SUBSTITUTE OATH OR DECLARATION must be submin			OTICE OF
8. CORRECTED DRAWINGS must be submitted. (a) including changes required by the Notice of Draftsper. 1) hereto or 2) to Paper No (b) including changes required by the proposed drawing or content of the proposed drawing or content or co	correction filed, wh	ich has been approved by the E	
(c) ☐ including changes required by the attached Examiner	's Amendment / Comment	or in the Office action of Paper N	10
Identifying indicia such as the application number (see 37 CFR 1 each sheet. $$.84(c)) should be written on	the drawings in the front (not the	back) of
9. DEPOSIT OF and/or INFORMATION about the depo- attached Examiner's comment regarding REQUIREMENT FOR T	SIT OF BIOLOGICAL MAT HE DEPOSIT OF BIOLOG	FERIAL must be submitted. N BICAL MATERIAL.	ote the
Attachment(s)			
 1⊠ Notice of References Cited (PTO-892) 3□ Notice of Draftperson's Patent Drawing Review (PTO-948) 5□ Information Disclosure Statements (PTO-1449), Paper No 7□ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	4∏ Intervie 6⊠ Examir	of Informal Patent Application (Few Summary (PTO-413), Paper I ner's Amendment/Comment ner's Statement of Reasons for A	No

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Examiner's Amendment

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided

by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be

submitted no later than the payment of the issue fee.

2. Applicant's election without traverse of Invention I, Species (a), claims 1-9, in the

Election filed August 18, 2003 is acknowledged.

3. Claims 10-27 are withdrawn from further consideration pursuant to 37 CFR

1.142(b) as being drawn to a nonelected Invention and/or Species, there being no

allowable generic or linking claim. Election was made without traverse in the Election

filed August 18, 2003.

4. This application is in condition for allowance except for the presence of claims

10-27 to Invention and/or Species non-elected without traverse. Accordingly, claims 10-

27 have been cancelled.

Reasons for Allowance

5. The following is an examiner's statement of reasons for allowance:

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A method of determining gate oxide thickness of a MOSFET by the combination and sequence of steps of:

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- Coupling the drain and source nodes to ground;
- Applying a range of voltages at the gate node;
- Measuring the gate direct tunneling current for each applied voltage to generate measured data; and
- Determining the gate oxide thickness by fitting a gate direct tunneling model to the measured data using a gate oxide thickness variable as a fitting parameter;

As further described in claim 1 has not been found.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Lagowski et al (6538462) shows a method of determining thickness of dielectric film on a silicon wafer using current-dielectric voltage characteristics with gate oxide integrity (GOI) techniques.

Smayling et al (5798649) and Abadeer et al (6188234) show methods of detecting defects in an insulator upon the gate of a MOS Capacitor or NFET/PFET transistor respectfully.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Russell Kobert whose telephone number is (703) 308-5222.

Any inquiry of a general nature or relating to the status of this application should be directed to the Group receptionist whose telephone number is (703) 308-0956.

Russell M. Kobert Patent Examiner Group Art Unit 2829 September 9, 2003

PRIMARY EXAMINER